



# EMC update, status and request

# C. Cecchi

**OUTLINE**:

- crystals
- mechanics
- electronics
- test of the electronics at BTF
- plans
- request

Gobain: 12 crystals received for the beam test

- Metrology to check dimension ok, new production within +0, -200 $\mu$ m (goal +0, -100  $\mu$ m)
- LY measurement ok, 1000 pe/MeV

• Uniformity very preliminary measurement, very good

# SIPAT: new production (3 samples L10-L11-L12) has just been tested

- Dimensions OK (improvement w.r.t. L8-L9)
- L10 absorption problem (will return to SIPAT)
- L11-L12 good transmittance, LY and resolution

After resolving absorption issue their LY is increased by 35% Improvement of the LY uniformity is still necessary Schedule is to be ready for October TB

#### NEXT:

exchange SIPAT crystals with St. Gobain ones to compare results (Perugia – Caltech should agree on set of measurements and procedure)

Weshave started in Perugia the measurement of LY uniformity of all the samples





Prototype structure for BT ready
Development is ongoing for the whole structure

- Production method working
- Precision within tolerances

What remains:

- Cost estimate in view of the 180 modules of
- a full endcap is available (1M euro)
- production schedule 1 year
- optical performance (to be studied with single cells)

• structural behaviour (module elastic characterisation, FEA of the support shell....)

We have ordered a second prototype structure for stress test at CERN

Measurement of single crystals in a single cell is starting to test LY uniformity  $\rightarrow$  will allow to study optical properties of the material

We are well on the way towards the construction of the whole structure.



Perudia

**READOUT, VFE, DAQ** 

**Suffinal** choice between PiN diodes (as in the Barrel) and APD's has not yet been done:

PiN would require intermediate step with PMT during uniformity measurements

## •APD's strong temperature dependence

New: neutron induced signal in APD's worse by a factor of 10 in PiN than in APD's To solve this problem it would be sufficient to read separately the signal from photodetectors and compare them, is it possible to do it also with PiN diodes? Study if the signal (w.r.t. noise) at low energy is sufficient  $\rightarrow$  we are going to test it in September.

VFE board delivered June 7<sup>th</sup>

Test in lab + Frascati of these new electronics board has started June

21<sup>st</sup>





Perugia









VEE Up for PIN

•VFE Up for PIN •VFE Down for APD







VFE boards received and tested (refer to next slides for results) Small optimization is needed in the cabling and shielding, it has started last week.

Perugia

INFN

• VME has not been tested in Frascati, boards have been delivered and tests have started and will continue during July.

• Software for the VME has to be written (A. Rossi with some help in Rome1 (V. Bocci) + new collaboration with Rome 3 (P. Branchini et al.))

A very important discussion has been started, triggered by the results on the background study in the barrel, due to the long decay time of the CsI(TI). We need a detailed study based on simulation to understand the best solution for the timing of the EMC to avoid pile up beteween signal and bckg. DETAILED STUDY OF SHAPING TIME AND TIME WINDOWS.

WHERE WE ARE.....





APD's have been monitored in temperature with 3 sensors VFE board has been tested

Ring8	Ring9	Ring10
PiN3	PiN2	PiN1
APD3	APD2	APD1

- Only 3 shapers (100ns) available
- Two different configuration:
  - PiNs connected to shapers
  - APDs connected to shapers
- For each configuration are acquired data at 500, 400, 300 and 200 MeV







Resolution

**APD vs PIN** 



About the same resolution for PiN and APD

 Difference is due to the fact that for APD beam is centered better than for PiN







# Linearity and resolution







THE GOAL is to be ready with 25 channels of the new electronics for October BT

- •Test LY and uniformity of all the cyrstals, exchange with Caltech on type 8 (July)
- Optimization of the VFE (July)
- Test of VME board in lab (to be finished by end of July)
- Modify the front panel for the 25 channels (August)
- Cabling of the 5 boards (August)
- VME software (August)
- Test of VME + cabling + integration of the system (September)





	PERUGIA	ROMA1	ROMA3
MI			
	VISITE RIBA 3 keuro		
	TEST BEAM 4 keuro		
ME			
	1 meeting USA 4 persone 10 keuro	TB CERN 7.5 keuro	TB CERN 3 keuro
	TB CERN 3 settimane 17 keuro		
CONSUMI			
	Elettronica + CsI per test 2 keuro		
INV			
			Process. VME 4 keuro

# ROMA 3 è una nuova richiesta dopo il loro ingresso in superB e partecipazione al TB al CERN per il DAQ

9 Luglio 2010

Riunione referee





**Continue developing on electronics:** 

- background suppression
- neutron signal in APD's and PiN's
- developing boards in view of the final micro ASIC for the VFE

Development of analog and digital components of the boards.

Starting procurement of crystals

Start construction of the mechanical structure

Finalize TDR

**Convenership of EMC** 

# PLANNING 2011 (ROMA1)

**Elettronica EMC (Coordinamento e LAB elettronica):** 

- Sviluppo digitizzazione (schede)
- Sviluppo pretrigger (sommatori, link ottici)
- Schede con differenti shaping times
- Ulteriori PIN/APD

Cristalli EMC:

- Test con differenti cristalli (Csl)
- Scelta e validazione produttori

# **ANAGRAFICA**

# PERUGIA

- 30% Resp. Loc. [ Conv. EMC] Claudia Cecchi RU •
- **Pasquale Lubrano** DR 30% ٠
- Stefano Germani 40% art.23 ٠
- Elisa Manoni 50% Ass. ۲
- Daniele Rinaldi Ric 50% •

# 2.0 FTE

#### + tecnici Laboratorio Elettronica e officina meccanica

#### ROMA1

Faccini Riccardo RU **30% Resp. Loc.** [ Conv. Spettroscopia] • 10%

20%

- Fernando Ferroni PO •
- Martellotti Giuseppe DR •
- 20% Pinci Davide Ric •
- **Auriemma Giulio** PO 20% •
- 10% [Resp. Elettronica EMC] **Bocci Valerio** Tecn •

# 1.1 FTE

#### + tecnici Laboratorio Elettronica







	Perugia (2FTE)	Roma1 (1.3 FTE)
MI		
	VISITE RIBA 3 keuro	PG ELETTRONICA 3 keuro
	ROMA ELETTRONICA 5 keuro	COLL. MEETING 2.5 keuro
	COLL. MEETING 3.5 keuro	
ME		
	1 MEETING USA 10 keuro	1 MEETING USA 7.5 keuro
	VIAGGI CRISTALLI 10 keuro	VIAGGI CRISTALLI 10 keuro
CONSUMI		
	SVILUPPO VFE 30 keuro	CRISTALLI 5 keuro
		ELETTR. 30 keuro
COSTR. APP.		
	CRISTALLI 470 keuro	
	MECCANICA 89 keuro	
7 LUXIIO 2010	PROGETTO MECC. 24 keuro	

•				Peruç	gia
nerA	Stima costi VFE				NFN
	Sviluppo ing Circuito stamp VFE	1	9000	9000	Istituto Nazionale
	costo attrezzatura	1	2000	2000	di Fisica Nuclear
	setup montaggio	5	800	4000	
	costo schede	5	400	2000	
	costo montaggio	5	350	1750	
	costo componenti	25	350	8750	
	Consumi vari in laboratorio		2500	2500	
			Totale	30000	

- 1 Sviluppo del PCB circuito compatto a 6-8 layers
- 2 Costo della attrezzatura (in ditta) per la realizzazione del PCB
- 3 set up per il montaggio delle schede
- 4 costo unitario di produzione del PCB VBFE
- 5 costo montaggio dei componenti su una scheda
- 6 costo unitario a canale dei componenti
- 7 consumi vari per cavi, attrezzature ecc.

Su



Stima costo Digitalizzatori	qty	costo unitario	costo totale
costo attrezzatura	1	1500	1500
setup montaggio	1	700	700
costo per schede	6	300	1800
costo montaggio	6	250	1500
stima componenti costo x ch	30	150	4500
		-	
		lotale	10000
Digitalizzatori commerciali			
Soluzione commerciale 25 ch	25	650	16250
Sviluppo pretrigger (sommatori, lin	k ottici) – 10K		
costo attrezzatura	1	1500	1500
setup montaggio	1	700	700
costo per schede	4	300	1200
costo montaggio	4	250	1000
costo link tx	1	1500	1500
costo link rx computer	1	1500	1500
stima componenti costo x ch	30	50	1500
		Totale	8000
			0900
Costi shaping prototipi			
costo attrezzatura	1	1500	1500
setup montaggio	1	700	700
costo schede	10	40	400
costo montaggio	10	70	700
costo componenti	10	150	1500
		Totale	4800
PIN o APD	40	100	4000

